

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

ANDREW M. WARWICK

GB 000029

Serial No.

Filed: CONCURRENTLY

TRENCH-GATE SEMICONDUCTOR DEVICES

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please
amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

7. (Amended) A semiconductor device as claimed in claim 1, wherein
a patterned insulating layer is provided on the semiconductor body,
wherein in the active cell area the insulating layer provides an
insulating overlayer on the trench-gates and the insulating layer
has windows where the source electrode contacts the source regions,
and wherein in the inactive area a window in the insulating layer
provides the gate electrode contact area.

8. (Amended) A semiconductor device as claimed in claim 1, wherein
in the active cell area an insulating layer is provided in the
trenches between the gate material in the trenches and the
semiconductor body adjacent the trenches.

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